

FIG. 1A

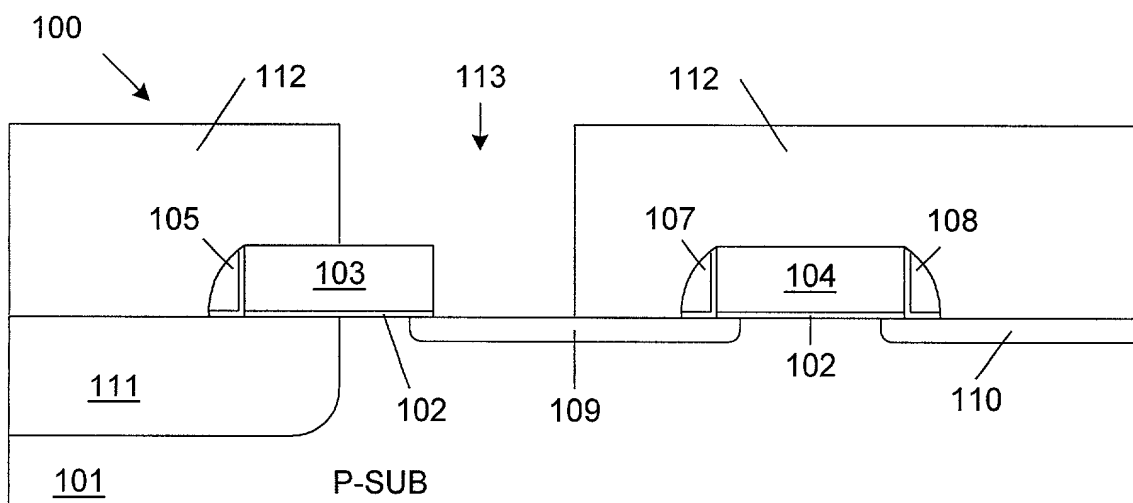


FIG. 1B

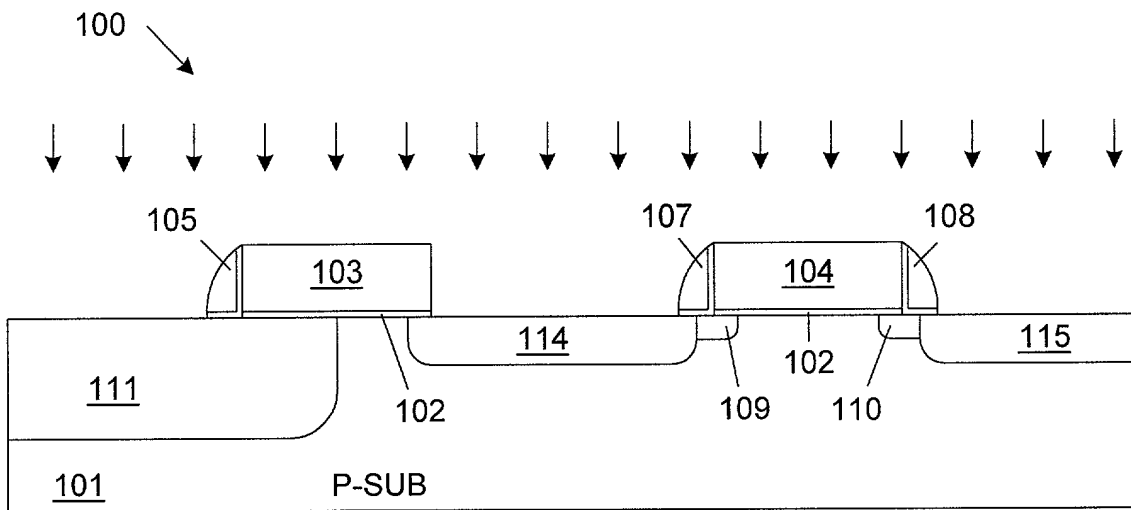


FIG. 1C

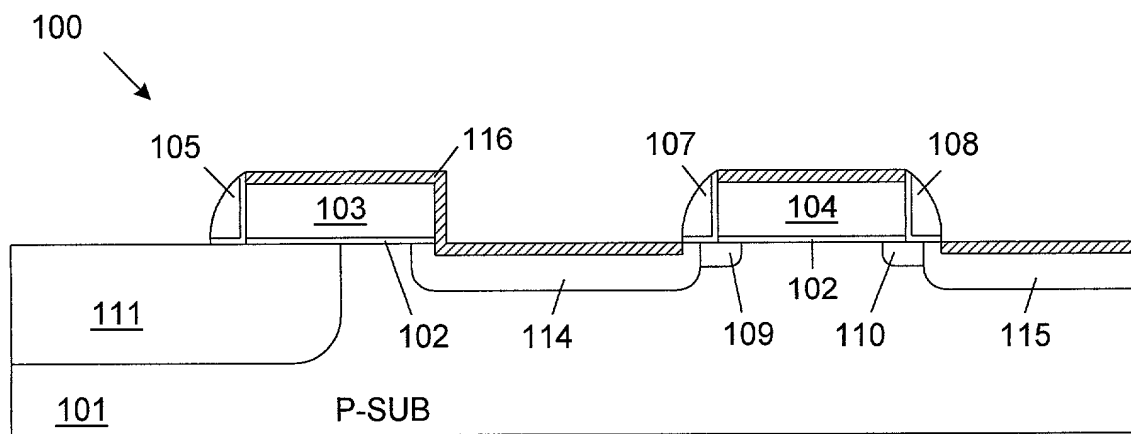


FIG. 1D

A cross-sectional view of a semiconductor device. A substrate 201 is labeled "P-SUB". A layer 202 is on top of the substrate. Two gate electrodes, 204 and 205, are on top of layer 202. Gate electrode 204 is on the left, and gate electrode 205 is on the right. A layer 203 is on top of gate electrode 205. A layer 206 is on top of gate electrode 204. A layer 207 is on top of the substrate 201. A layer 208 is on top of the substrate 201. A layer 209 is on top of the substrate 201. A layer 210 is on top of the substrate 201. A layer 211 is on top of the substrate 201. A layer 212 is on top of the substrate 201. A layer 213 is on top of the substrate 201.

FIG. 2C

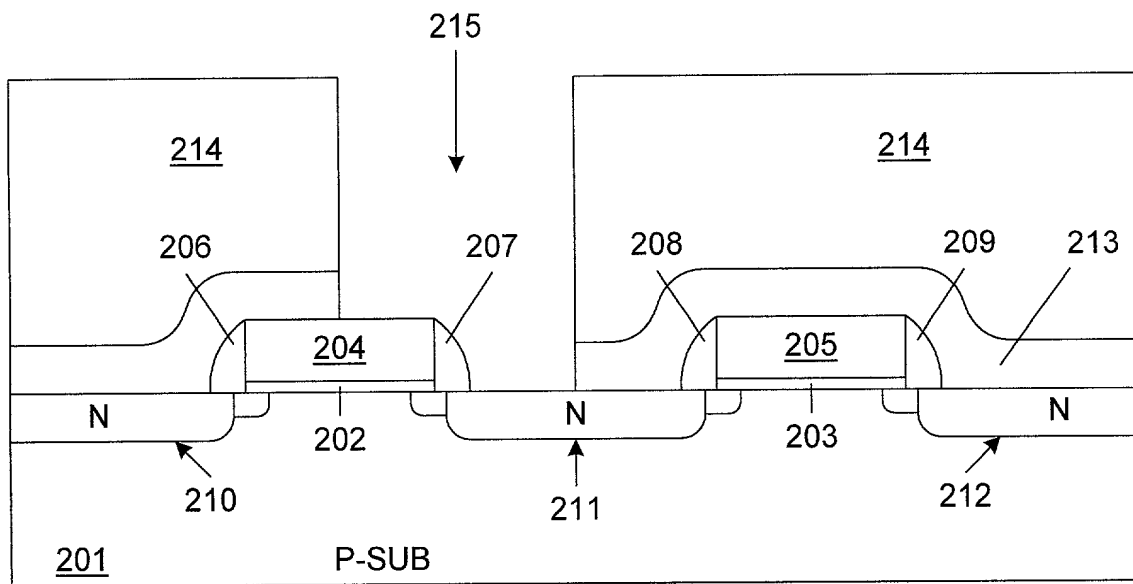


FIG. 2D

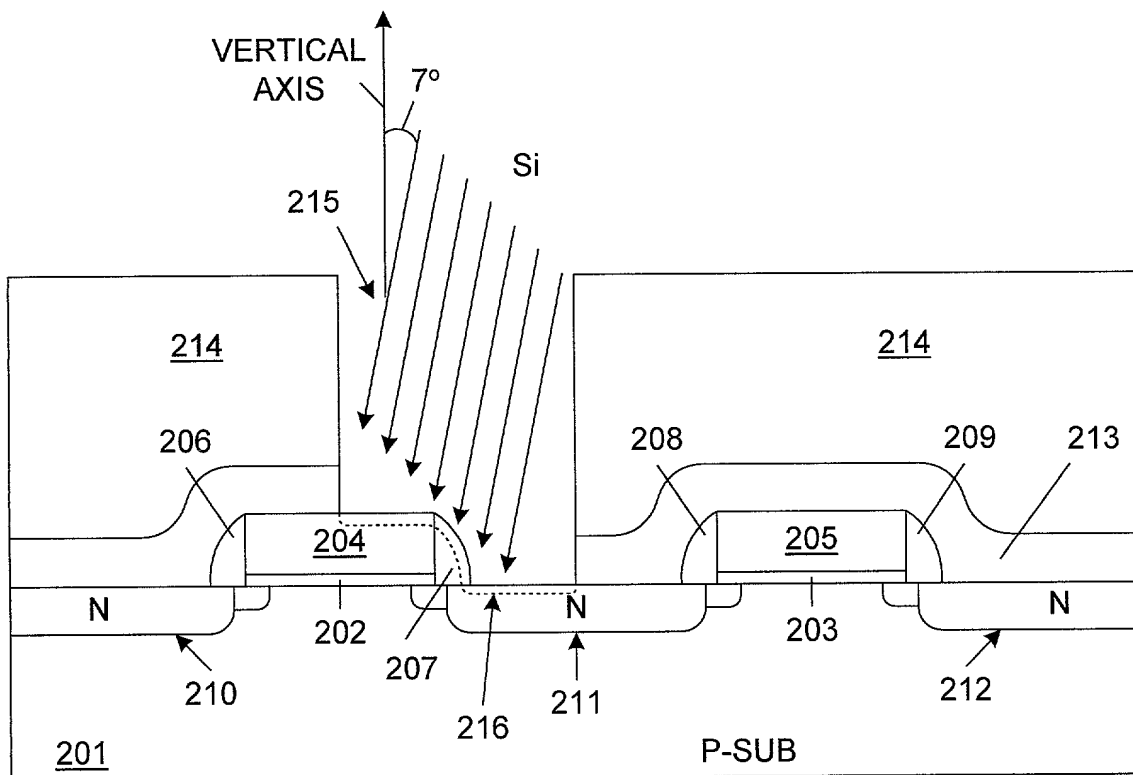


FIG. 2E

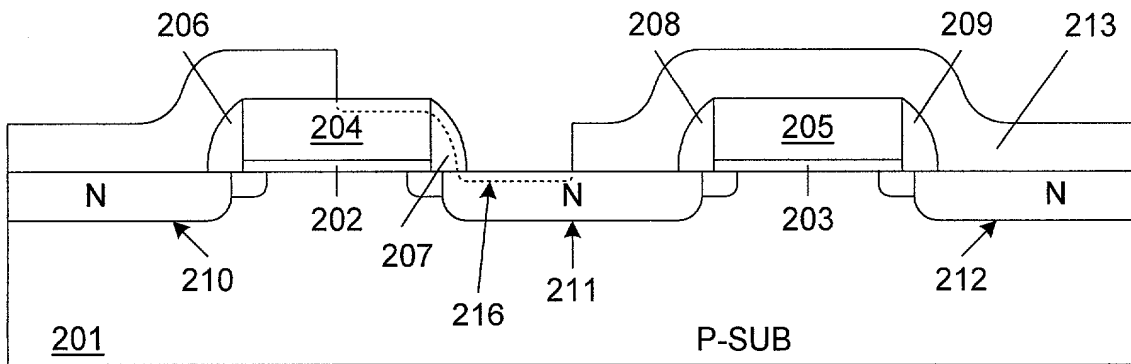


FIG. 2F

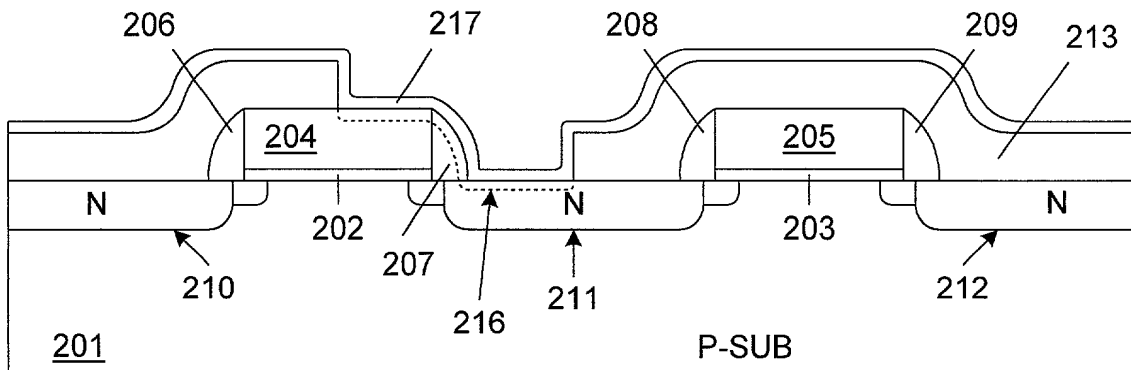


FIG. 2G

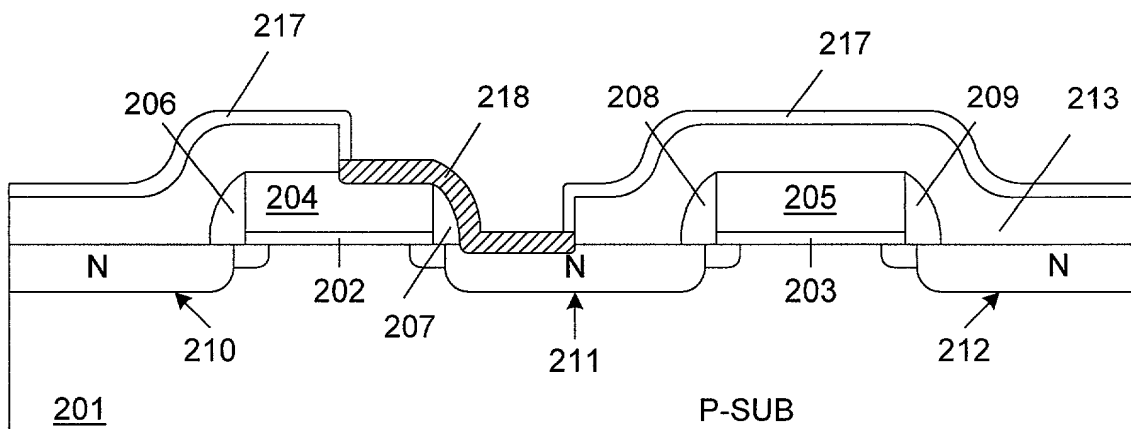


FIG. 2H

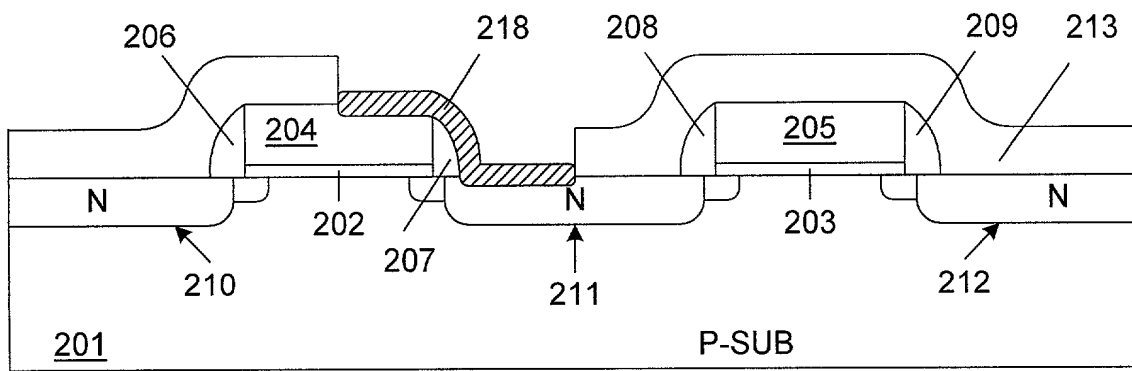


FIG. 2I